

DIODE ARRAY PRODUCT SPECIFICATION

MONOLITHIC AIR ISOLATED DIODE ARRAY

FEATURES:

- HERMETIC CERAMIC PACKAGE
- $V_b > 75V$ at 5uA
- $I_r < 100nA$ at 40V
- $C < 4.0$ pF

Absolute Maximum Ratings:

Symbol	Parameter	Limit	Unit
VBR(R) *1 *2	Reverse Breakdown Voltage	75	Vdc
IO *1 *3	Continuous Forward Current	300	mAdc
IFSM *1	Peak Surge Current (tp= 1/120 s)	500	mAdc
PT1 *4	Power Dissipation per Junction @ 25°C	400	mW
PT2 *4	Power Dissipation per Package @ 25°C	600	mW
Top	Operating Junction Temperature Range	-65 to +150	°C
Tstg	Storage Temperature Range	-65 to +200	°C

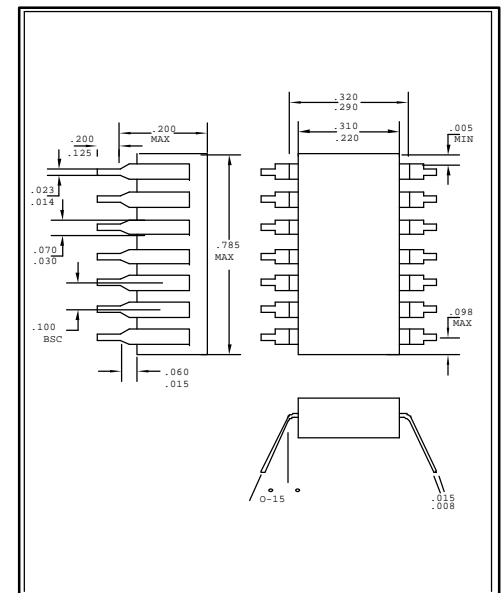
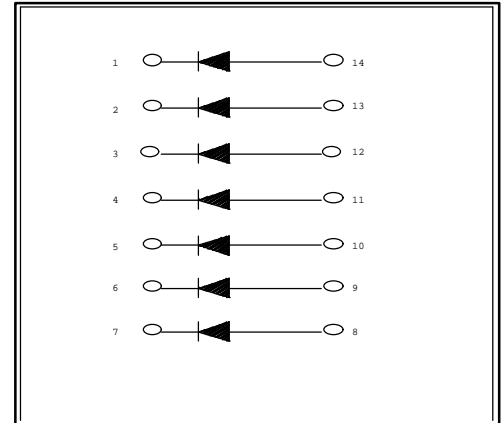
NOTE 1: Each Diode

NOTE 2: Pulsed: PW = 100ms max.; duty cycle \leq 20%

NOTE 3: Derate at 2.4mA/°C above +25 °C

NOTE 4: Derate at 4.0mW/°C above +25 °C

Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified



PACKAGE OUTLINE

Symbol	Parameter	Conditions	Min	Max	Unit
Vf1	Forward Voltage	$I_f = 100mAdc$ *1		1	Vdc
IR1	Reverse Current	$V_R = 40$ Vdc		0.1	uAdc
IR2	Reverse Current	$V_R = 20$ Vdc		25	nAdc
Ct	Capacitance (pin to pin)	$V_R = 0$ Vdc ; $f = 1$ MHz		4.0	pF
tfr	Forward Recovery Time	$I_f = 100mAdc$		15	ns
trr	Reverse Recovery Time	$I_f = I_R = 10mAdc$, $i_{rr} = 1$ mAdc, $R_L = 100$ ohms		10	ns
VF5	Forward Voltage Match	$I_f = 10$ mA		5	mV

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle \leq 2%, 90us after leading edge

Sertech reserves the right to make changes to any product design, specification or other information at any time without prior notice.